Supporting Information for

Hierarchically Porous Carbon with Controlled Structure for Efficient Microwave Absorption

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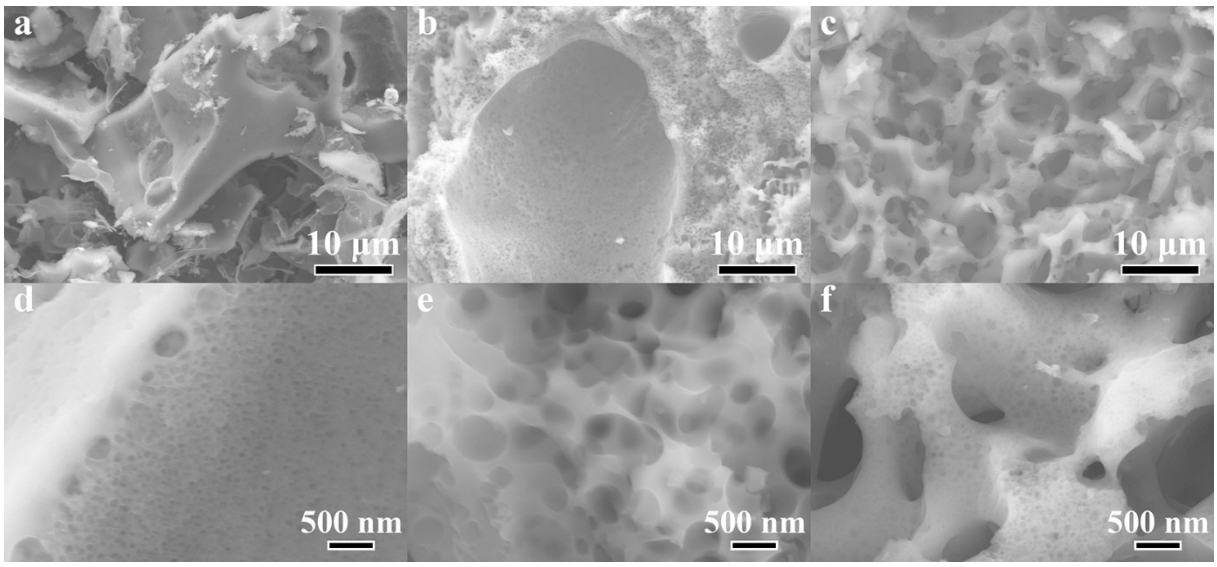

Figure S1. SEM images of (a and d) CP-0-1; (b and e) CP-0.4-1 and (c and f) CP-0.8-1.

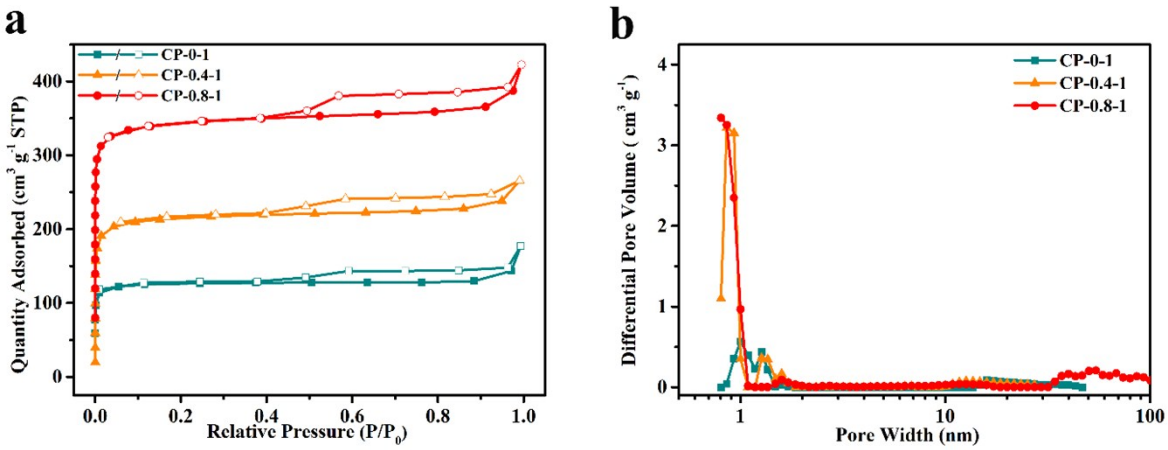

Figure S2. (a) Nitrogen adsorption-desorption isotherms and (b) pore size distribution calculated using DFT method of CP-x-1.

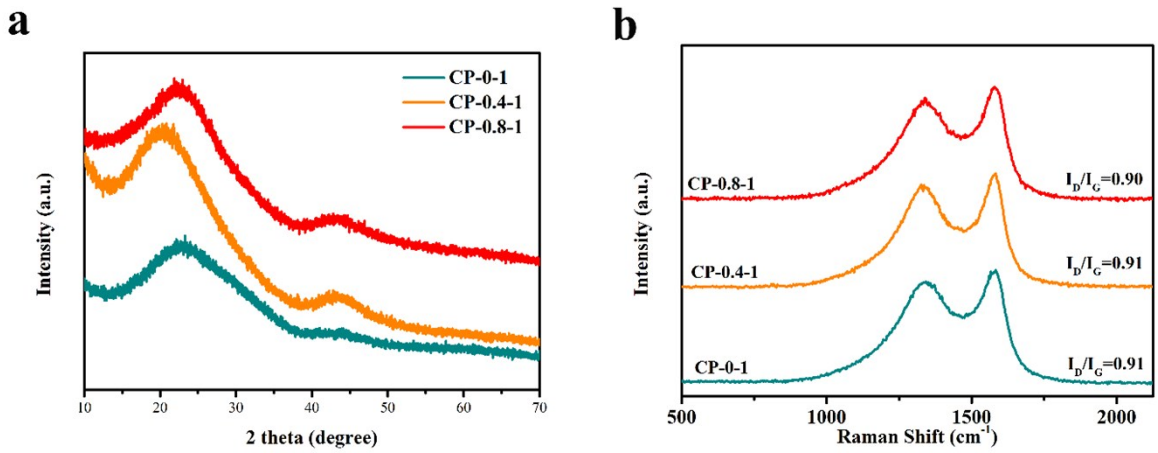

Figure S3. (a) XRD patterns and (b) Raman spectra of CP-x-1 prepared using precursors with different water phase volume fractions.

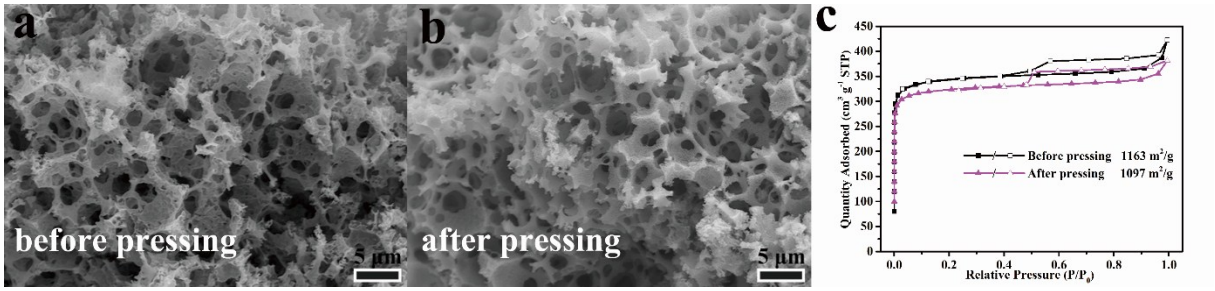

Figure S4. The SEM figures (a and b) and N2 absorption-desorption isotherms (c) of CP-0.8-1 before and after pressing procedure. The sample after pressing procedure is prepared by immersing the test sample of CP-0.8-1 in hexane to remove the paraffin. It is obvious that these two samples possess almost the same micro-sized porous structure and N2 absorption-desorption isotherm (nano-sized porous structure), suggesting that the pressing process has negligible influence on the porous structure.

Table S1. MA performance of representative MA materials reported previously and CP-0.8-1

absorbents	thickness (mm)	RL_{max} (−dB)	EAB (GHz)
Fe_3O_4/graphene[1]	3.5	-32.0	4.5
PPy@PANI-1.2[2]	2.0	−34.8	4.7
RGO/$MnFe_2O_4$/PVDF[3]	3.0	-29.0	4.9
$BaTiO_3$[4]	2.0	−21.8	1.8
C@Fe@Fe_3O_4[5]	1.5	−40.0	5.2
Fe_3O_4–graphene[6]	4.5	−40.0	2.3
TiO_2[7]	4.0	-36.9	1.0
Fe/C[8]	2.0	-22.6	5.3
CP-0.8-1 (this work)	2.46	−56.4	6.0

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